## QIAOXIN N-Channel Super Trench Power MOSFET

### Description

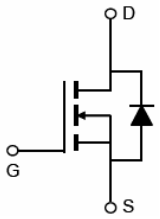
The VCRRP0116K uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and $Q_g$. This device is ideal for high-frequency switching and synchronous rectification.

### General Features

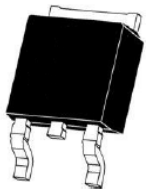
- $V_{DS}$ =100V,$I_D$ =16A
  $R_{DS(ON)}$=78mΩ (typical) @ $V_{GS}$=10V
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating
- 100% UIS tested

### Application

- LED backlighting
- Ideal for high-frequency switching and synchronous rectification




**Schematic diagram**



**TO-252 -2Ltop view**

### Package Marking and Ordering Information

| Device Marking | Device | Device Package |
|---|---|---|
| VCRRP0116K | | TO-252-2L |

### Absolute Maximum Ratings ($T_A$=25℃unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|---|---|---|
| Drain-Source Voltage | $V_{DS}$ | 100 | V |
| Gate-Source Voltage | $V_{GS}$ | ±20 | V |
| Drain Current-Continuous | $I_D$ | 16 | A |
| Drain Current-Continuous($T_C$=100℃) | $I_D$ (100℃) | 11.3 | A |
| Pulsed Drain Current | $I_{DM}$ | 64 | A |
| Maximum Power Dissipation | $P_D$ | 55 | W |
| Derating factor | | 0.37 | W/℃ |
| Single pulse avalanche energy (Note 5) | $E_{AS}$ | 26 | mJ |
| Drain Source voltage slope, $V_{DS}$ ≤120 V, | dv/dt | 50 | V/ns |
| Drain Source voltage slope, $V_{DS}$ ≤120 V, $I_{SD}$<$I_D$ | dv/dt | 50 | V/ns |
| Operating Junction and Storage Temperature Range | $T_J$,$T_{STG}$ | -55 To 175 | ℃ |

## Thermal Characteristic

| | | | |
|---|---|---|---|
| Thermal Résistance, Junction-to-Case(Note 2) | $R_{\theta JC}$ | 2.7 | ℃/W |

## Electrical Characteristics ($T_A$=25℃unless otherwise noted)

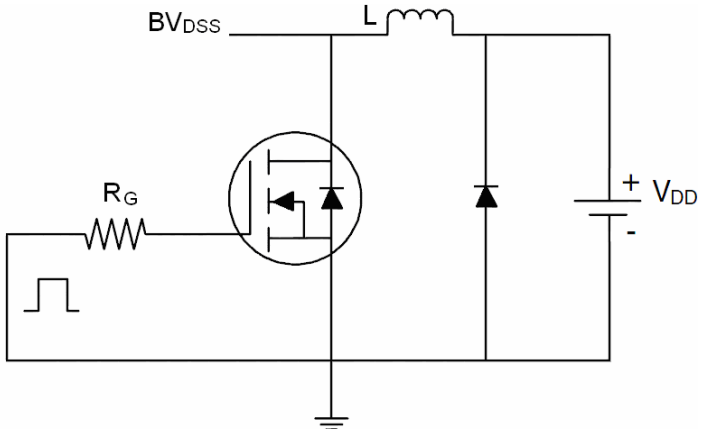
| Parameter | Symbol | Condition | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **Off Characteristics** | | | | | | |
| Drain-Source Breakdown Voltage | $BV_{DSS}$ | $V_{GS}$=0V $I_D$=250μA | 100 | - | - | V |
| Zero Gate Voltage Drain Current | $I_{DSS}$ | $V_{DS}$=100V,$V_{GS}$=0V | - | - | 1 | μA |
| Gate-Body Leakage Current | $I_{GSS}$ | $V_{GS}$=±20V,$V_{DS}$=0V | - | - | ±100 | nA |
| **On Characteristics** (Note 3) | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}$=$V_{GS}$,$I_D$=250μA | 2.0 | 3.2 | 4.0 | V |
| Drain-Source On-State Resistance | $R_{DS(ON)}$ | $V_{GS}$=10V, $I_D$=16A | - | 78 | 95 | mΩ |
| Gate resistance | $R_G$ | | - | 10 | - | Ω |
| Forward Transconductance | $g_{FS}$ | $V_{DS}$=5V,$I_D$=16A | - | 20 | - | S |
| **Dynamic Characteristics** (Note4) | | | | | | |
| Input Capacitance | $C_{lss}$ | $V_{DS}$=50V,$V_{GS}$=0V, F=1.0MHz | - | 322 | | PF |
| Output Capacitance | $C_{oss}$ | | - | 53 | | PF |
| Reverse Transfer Capacitance | $C_{rss}$ | | - | 5.1 | | PF |
| **Switching Characteristics** (Note 4) | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}$=50V, $R_L$=3Ω $V_{GS}$=10V,$R_G$=3Ω | - | 6 | - | nS |
| Turn-on Rise Time | $t_r$ | | - | 3 | - | nS |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 18 | - | nS |
| Turn-Off Fall Time | $t_f$ | | - | 3 | - | nS |
| Total Gate Charge | $Q_g$ | $V_{DS}$=50V,$I_D$=10A, $V_{GS}$=10V | - | 5.6 | - | nC |
| Gate-Source Charge | $Q_{gs}$ | | - | 2.4 | - | nC |
| Gate-Drain Charge | $Q_{gd}$ | | - | 1.3 | - | nC |
| **Drain-Source Diode Characteristics** | | | | | | |
| Diode Forward Voltage (Note 3) | $V_{SD}$ | $V_{GS}$=0V,$I_S$=10A | - | - | 1.2 | V |
| Diode Forward Current (Note 2) | $I_S$ | | - | - | 16 | A |
| Reverse Recovery Time | $t_{rr}$ | $T_J$ = 25°C, $I_F$ = $I_S$ di/dt = 100A/μs(Note3) | - | 15 | - | nS |
| Reverse Recovery Charge | Qrr | | - | 53 | - | nC |

## Notes:

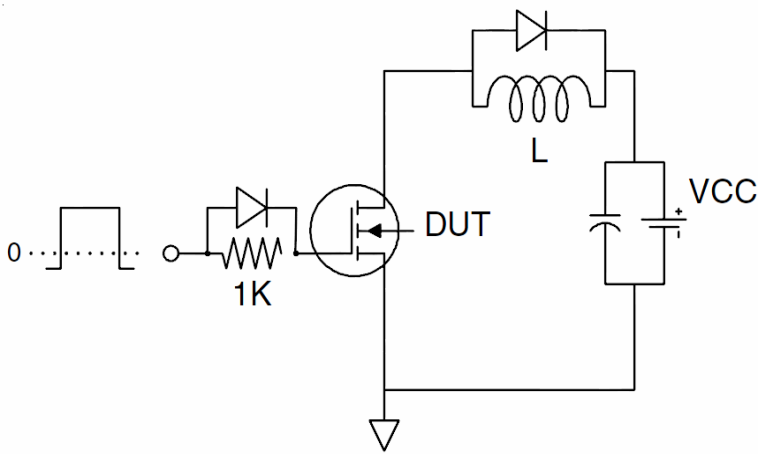
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production
5. EAS condition : Tj=25℃,$V_{DD}$=50V,$V_G$=10V,L=0.5mH,Rg=25Ω

## Test Circuit

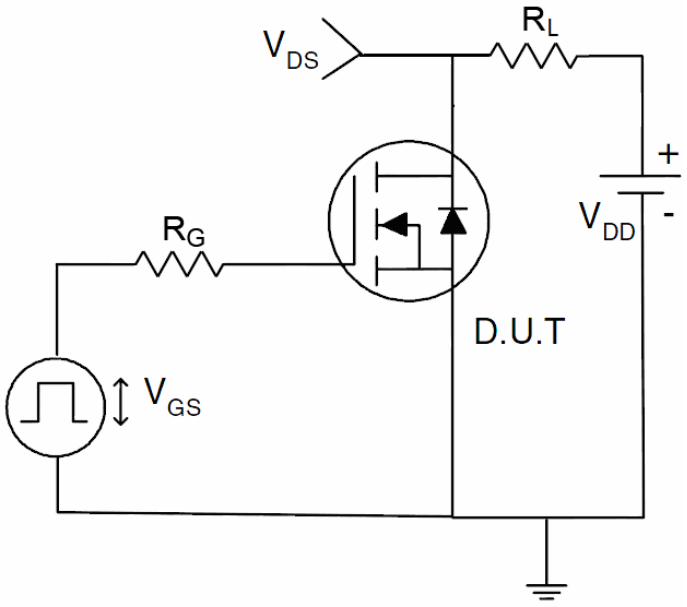
### 1) $E_{AS}$ test Circuit




### 2) Gate charge test Circuit




### 3) Switch Time Test Circuit



## Typical Electrical and Thermal Characteristics

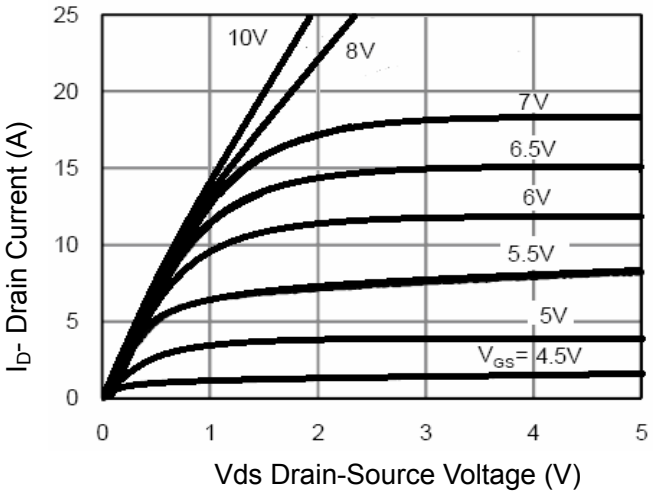



**Figure 1 Output Characteristics**

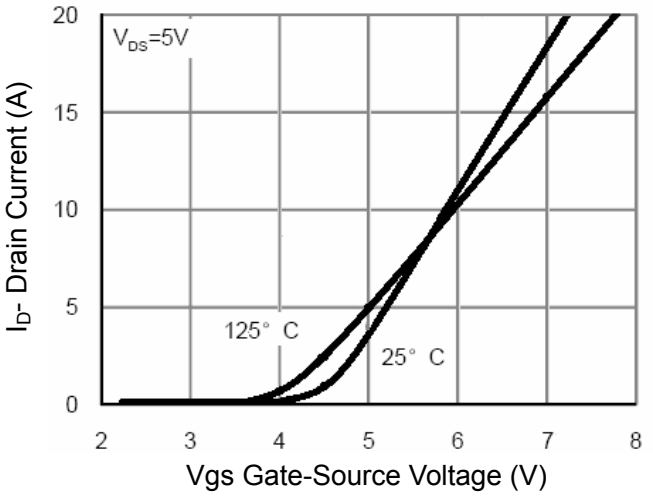



**Figure 2 Transfer Characteristics**

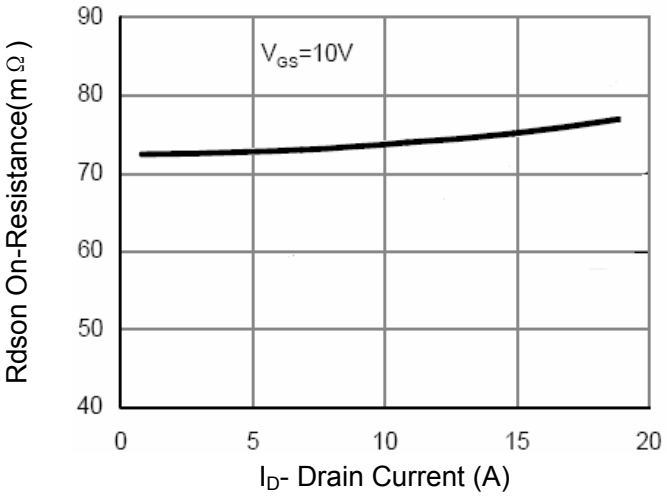



**Figure 3 Rdson- Drain Current**

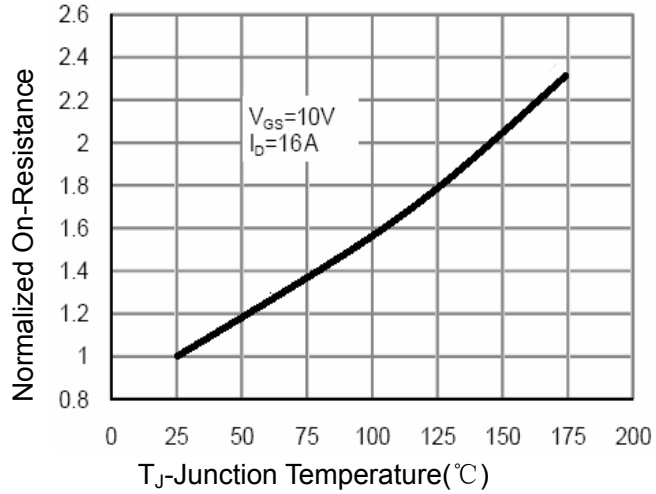



**Figure 4 Rdson-Junction Temperature**

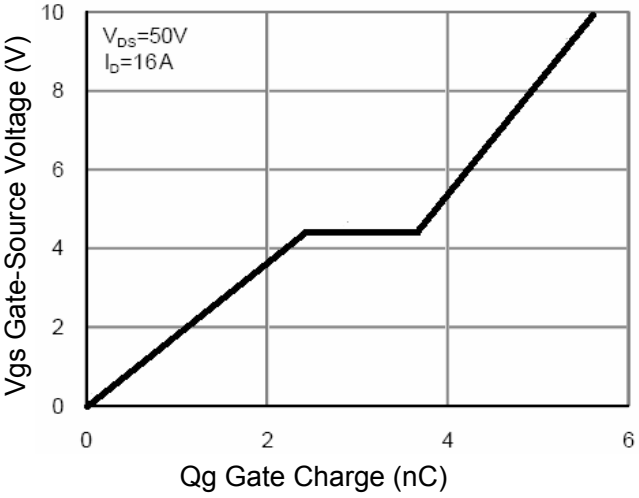



**Figure 5 Gate Charge**

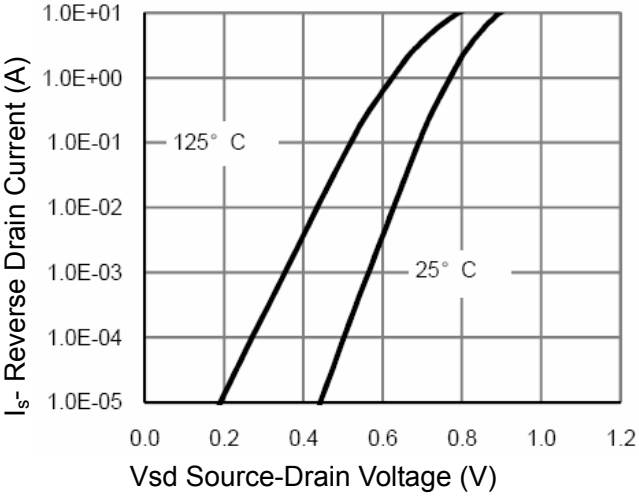



**Figure 6 Source- Drain Diode Forward**

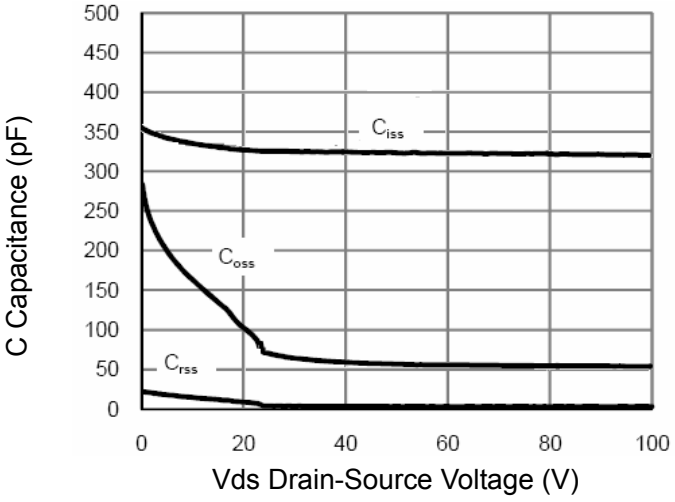



**Figure 7 Capacitance vs Vds**

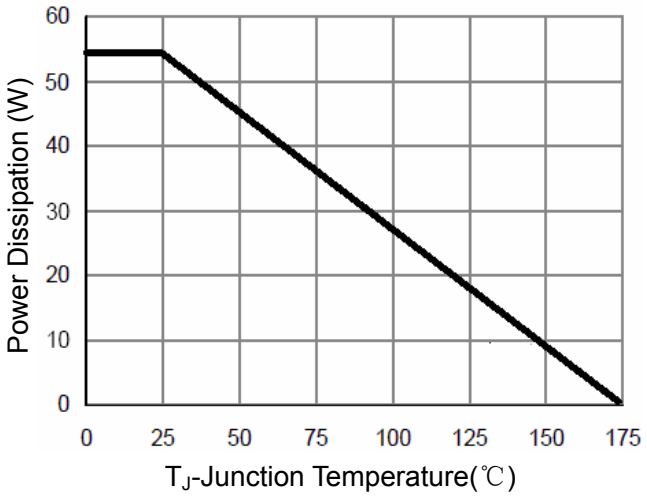



**Figure 9 Power De-rating**

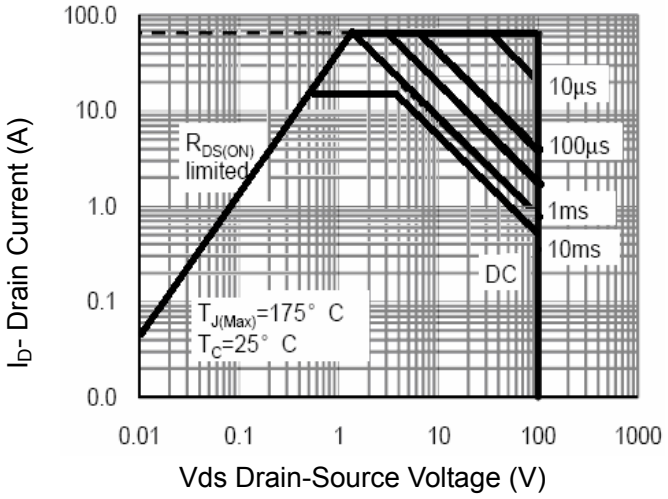



**Figure 8 Safe Operation Area**

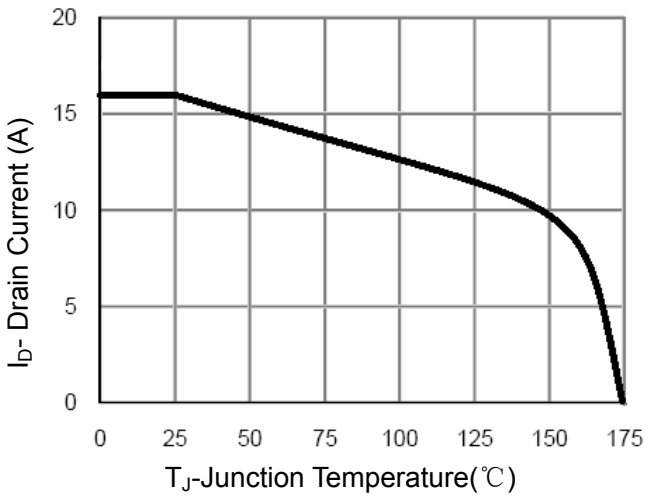



**Figure 10 Current De-rating**

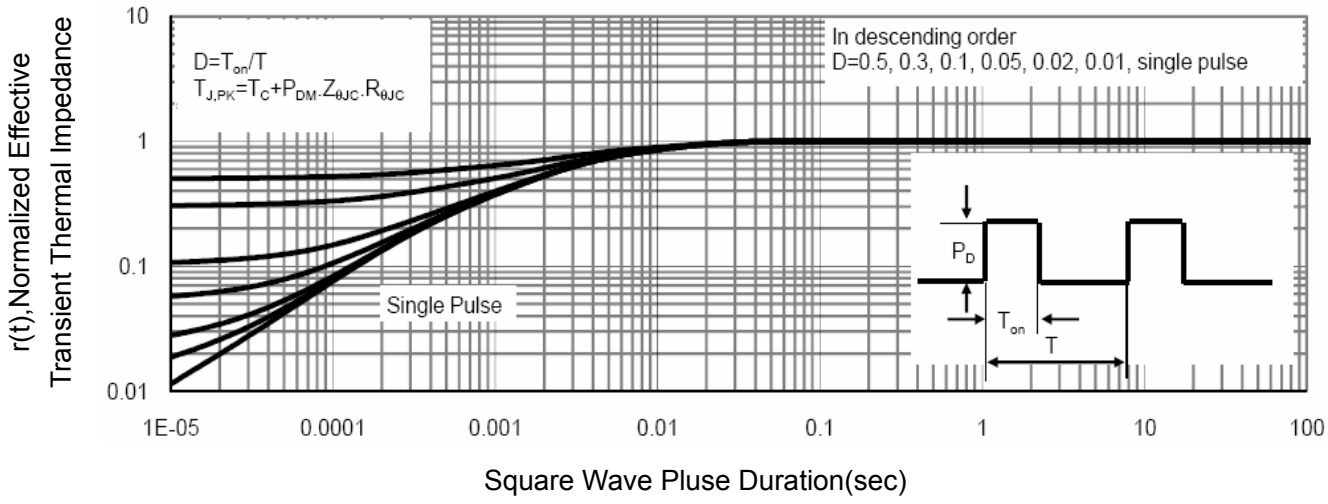



**Figure 11 Normalized Maximum Transient Thermal Impedance**

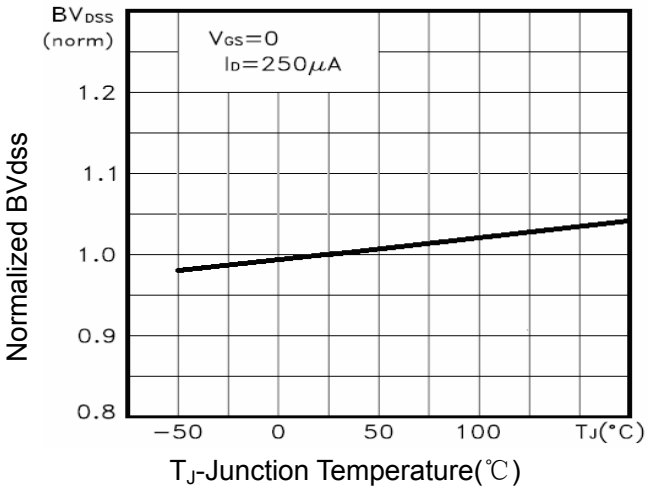
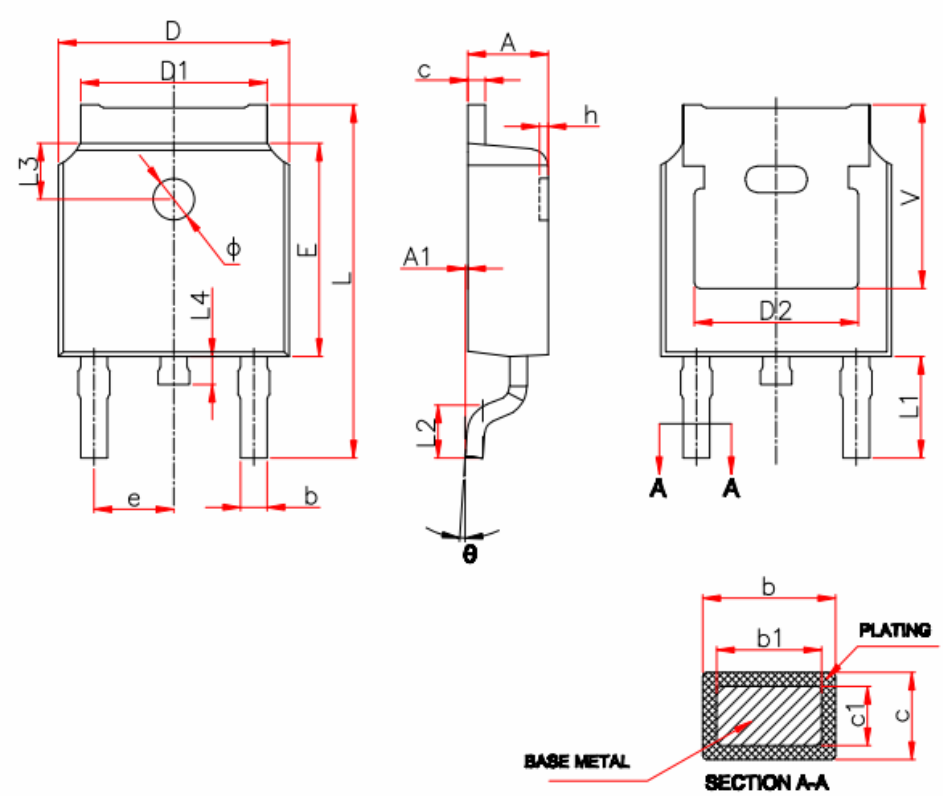



**Figure 12 $BV_{DSS}$ vs Junction Temperature**

## TO-252 Package Information




| Symbol | Millimeters | |
|---|---|---|
| | Min. | Max. |
| A | 2.20 | 2.40 |
| A1 | 0.00 | 0.13 |
| b | 0.66 | 0.86 |
| b1 | 0.73 | 0.79 |
| c | 0.46 | 0.58 |
| c1 | 0.50 | 0.52 |
| D | 6.50 | 6.70 |
| D1 | 5.10 | 5.46 |
| D2 | 4.83 REF. | |
| E | 6.00 | 6.20 |
| e | 2.19 | 2.39 |
| L | 9.80 | 10.40 |
| L1 | 2.90 REF. | |
| L2 | 1.40 | 1.70 |
| L3 | 1.60 REF. | |
| L4 | 0.60 | 1.00 |
| Φ | 1.10 | 1.30 |
| θ | 0° | 8° |

## Attention

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